Sheet 1 of 4 sheets

U.S. Department of Commerce, Patent and Trademark Office Serial No. 10/683937 Unassigned Docket No. (PTO Form 1449 modified) **APPM/8539** INFORMATION DISCLOSURE STATEMENT BY APPLICANT **Applicant** Confirmation No. Kim, et al. Unknown (Use several sheets if necessary) Group Filing Date 282~ Examiner Unknown **Unknown** Herewith **U.S. Patent Documents** *Examiner Document Issue Applicant(s) Class **Subclass** Filing Date If Initial Number Date Name **Appropriate** 6,544,900 **A1** 04/08/2003 Raaijmakers, et H01L 2131 11/14/2001 **A2** 6,458,718 10/01/2002 Todd 438 778 04/24/2001 **A3** 6,410,463 06/25/2002 Matsuki 438 790 10/18/2000 **A4** 6.383.955 05/07/2002 Matsuki, et al. 438 790 06/07/1999 **A5** 6.358,829 03/19/2002 Yoon, et al. 438 597 09/16/1999 A6 6,352,945 03/05/2002 Matsuki, et al. 438 778 06/07/1999 **A7** 6,348,420 02/19/2002 769 Raaijmakers, et 438 12/23/1999 al. **8A** 6,284,686 09/04/2001 Marlor 501 64 12/22/1999 **A9** 6,232,196 05/15/2001 Raaijmakers, et 438 386 03/05/1999 A10 6,025,627 02/15/2000 Forbes, et al. 257 321 05/29/1998 A11 5,807,792 09/15/1998 Ilg, et al. 438 758 12/18/1996 A12 5,796,116 08/18/1998 Nakata, et al. 257 66 07/25/1995 **Foreign Patent Documents** *Examiner Document Date Country Class Subclass **Translation** Initial Number YES NO MT **B1** 1 150 345 10/31/2001 EP H01L 21/316 \boxtimes П **B2** 2001-189312 05/02/2001 JP **C30B** 25/02 \boxtimes **B3** 63062313 03/18/1988 JP (abstract) H01L 21/203 \boxtimes **B4** 58098917 06/13/1983 JP H01L 21/205 冈 **OTHER ART** *Examiner Including Author, Title, Date, Initial Pertinent Pages, Etc. C1 Lee, et al., Cyclic technique for the enhancement of highly oriented diamond film growt, Elsevier Science S.A., Thin Solid Films (1997) 264-268. C2 Choi, et al., Stability of TiB2 as a Diffusion Barrier on Silicon. Electrochemical Society Vol. 138 No. 10 October 1991 " Examiner Mich **Date Considered** 6 *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

E003-10-10-5003

Sheet 2 of 4 sheets U.S. Department of Commerce, Patent and Trademark Office Docket No. Serial No. 10/683937 (PTO Form 1449 modified) APPM/8539 Unassigned INFORMATION DISCLOSURE STATEMENT BY APPLICANT **Applicant** Confirmation No. Kim, et al. Unknown (Use several sheets if necessary) Group Filing Date 2822 Examiner Unknown Herewith Unknown **U.S. Patent Documents** *Examiner **Document** Issue Applicant(s) Class **Subclass** Filing Date If Initial Number Date Name Appropriate A13 5,693,139 12/02/1997 Nishizawa, et 117 89 06/15/1993 al. A14 10/07/1997 5.674.304 Fukada, et al. 65 32.4 09/23/1994 A15 5,527,733 06/18/1996 Nishizawa, et 437 160 02/18/1994 al. A16 5,480,818 01/02/1996 Matsumoto, et 437 40 02/09/1993 al. **A17** 5,469,806 11/28/1995 Mochizuki, et 117 97 08/20/1993 A18 5,374,570 12/20/1994 Nasu, et al. 437 40 08/19/1993 A19 5,372,860 12/13/1994 427 Fehlner, et al. 578 07/06/1993 A20 5.294,286 03/15/1994 Nishizawa, et 156 610 01/12/1993 A21 4.834.831 05/30/1989 Nishizawa, et 156 611 09/04/1987 al. **Foreign Patent Documents** *Examiner Document Date Country Class Subclass Translation Initial Number YES NO **B**5 62-171999 07/28/1987 JP **C30B** 29/40 \boxtimes **B6** 2001-189312 JP 07/10/2001 H01L 21/316 П \boxtimes **B7** 2001-111000 04/20/2001 JP H01L 27/105 \boxtimes **B8** 5102189 04/23/1993 JP H01L X 21/336 OTHER ART *Examiner Including Author, Title, Date, Initial Pertinent Pages, Etc. C3 Paranjpe, et al., Atomic Layer Deposition of AIOx for Thin Film Head Gap Applications, ECS. Journal of the Electrochemical Society, 148 (9) G465-G471 (2001). **C4**

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3/3 Sheet 3 of 4 sheets

U.S. Department of Commerce, Patent and Trademark Office Docket No. Serial No. (0/683937 Unassigned (PTO Form 1449 modified) APPM/8539 INFORMATION DISCLOSURE STATEMENT BY APPLICANT **Applicant** Confirmation No. Kim, et al. Unknown Group 2822 (Use several sheets if necessary) Filing Date Examiner Unknown Herewith Unknown **U.S. Patent Documents** *Examiner Document Issue Applicant(s) Class **Subclass** Filing Date If Initial Number Date Name **Appropriate** m A22 2003/0082300 05/01/2003 Todd, et al. 427 255.27 02/11/2002 A23 2003/0036268 02/20/2003 Brabant, et al. **C30B** 1/00 05/29/2002 A24 2003/0022528 01/30/2003 Todd 438 933 02/11/2002 A25 2002/0197831 12/26/2003 Todd, et al. 438 528 02/11/2002 A26 2002/0173130 11/21/2002 Pomerede, et 438 592 04/10/2002 al. **A27** 2002/0173113 11/21/2002 Todd 438 398 02/11/2002 **A28** 2002/0168868 11/14/2002 Todd 438 767 02/11/2002 A29 2002/0093042 07/18/2002 257 303 Oh, et al. 11/13/2001 A29 2001/0055672 12/27/2001 Todd 428 212 02/07/2001 A30 2001/0046567 11/29/2001 427 Matsuki, et al. 578 04/06/2001 A31 2001/0024871 09/27/2001 438 604 Yagi 01/31/2001 A32 2001/0020712 09/13/2001 Raaiimakers, et 257 301 01/18/2001 al. **Foreign Patent Documents** *Examiner Document Date Country Class Subclass **Translation** Initial Number YES NO **B5** 62-171999 07/28/1987 JP C30B 29/40 \boxtimes **B6** 2001-189312 07/10/2001 JP H01L 21/316 \Box \boxtimes **B7** 2001-111000 04/20/2001 JP H01L \Box 27/105 冈 OTHER ART *Examiner Including Author, Title, Date, Initial Pertinent Pages, Etc. C3 **C4** لئ: Examiner viv **Date Considered** 05 *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet of | 1

Complete if Known						
Application Number	10/683,937					
Filing Date	October 10, 2003					
First Named Inventor	Kim et al.					
Art Unit	2812					
Examiner Name	Unassigned					
Attorney Docket Number	AMAT/8539/TSG/EPI/RKK					

		NON PATENT LITERATURE DOCUMENTS	, <u>.</u>
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
MT	C1	Article by Uchino et al., entitled "A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1-µm CMOS ULSIs", IEDM, December 1997, Technical Digest, pgs. 479-482.	
MT	C2	Article by Sedgwick et al., entitled "Selective SiGe and heavily as doped Si deposited at low temperature by atmospheric pressure chemical vapor deposition", Journal of Vacuum Science & Technology, May/June 1993, No. 3, pgs. 1124-1128.	
25 pr	СЗ	Article by Kamins et al., entitled "Kinetics of Selective epitaxial deposition Si _{1-a} Ge _a ", American Institute of Physics, 1992/August, No. 6, pgs. 669-671	
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	C 5		
	C6		
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	C8		
	C9		
	C10	·	
	C11		
	C12		
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Examiner Signature	Michael	Trid	Date Considered	8/13/05	

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ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

Method of Selective Deposition of Heavily Doped Epitaxial SiGe

Application Number:

10/683937

Confirmation Number:

2191

First Named Applicant:

Yihwan Kim

Attorney Docket Number:

AMAT8539TSGEPIRKK

Art Unit:

2812

Examiner:

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(6559520 or 6335280 or 20030189208).pn

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That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
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14	2	6335280	2002-01-01	van der Jeugd			

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init Cite.	No. Pub. No.	Date	Applicant	Kind	Class	Subclass
mat 1	20030189208	2003-10-09	Law et al.			

Signature

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Michael Trich

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10/683,937 Substitute for form 1449A/PTO **Application Number** Filing Date October 10, 2003 SUPPLEMENTAL INFORMATION First Named Inventor Kim, et al. DISCLOSURE STATEMENT BY APPLICANT Group Art Unit 2812 **Examiner Name** Michael M. Trinh (Use as many sheets as necessary) **Attorney Docket Number** AMAT/8539/TSG/EPI/RKK Sheet of 2 **Submission Date** April 21, 2005

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	Examiner	Cite	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where	
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Examiner Initials*	Cite	Foreign Patent Document	Publication Date	Name of Patentee or	Pages, Columns, Lines,	T⁵
	No.¹	Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Where Relevant Passages or Relevant Figures Appear	
por B1		WO 02/097864 A2	12/05/2002	ASM AMERICA, INC.		
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MT	C1	International Sea	arch Report mailed February 22, 2	005 for PCT/US2004/030872 (AMAT/853	9-PCT)	
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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number. 10/683.937 **Application Number** Substitute for form 1449A/PTO Filing Date October 10, 2003 SUPPLEMENTAL INFORMATION First Named Inventor Kim, et al. **DISCLOSURE STATEMENT BY APPLICANT Group Art Unit** 2812 **Examiner Name** Michael M. Trinh (Use as many sheets as necessary) AMAT/8539/TSG/EPI/RKK Attorney Docket Number Sheet 2 of 2 **Submission Date** April 21, 2005

	·	NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	country where published	T²
MT	C2	Jeong, et al. "Growth and Characterization of Aluminum Oxide (Al ₂ O ₃) Thin Films by Plasma-Assisted Atomic Layer Controlled Deposition," J. Korean Inst. Met. Mater., Vol. 38, No. 10, Oct. 2000 PP. 1395-1399	
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Examiner	Μ	wichael Trick Date Considered 6/13/65	

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